Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An anti-reflective coating forming composition, used for lithography process for manufacturing a semiconductor device comprising a compound of formula (1), a condensation product thereof or a resin produced from the compound

$$R_2OH_2C$$
 N
 CH_2OR_1
Formula (1)

wherein R₁ and R₂ are independently of each other hydrogen atom or an alkyl group, R₃ and R₄ are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxymethyl group, and an acid and/or acid generator, and the compound, the condensation product thereof or the resin produced from the compound is contained in an amount of 50 mass% or more in a solid content of the anti-reflective coating forming composition.

wherein the anti-reflective coating forming composition is an underlayer of a resist and subjected to dry etching.

- 2-3. (Canceled)
- 4. (Previously Presented) The anti-reflective coating forming composition according to claim 1, further containing a light absorbing compound and/or a light absorbing resin.
- 5. (Previously Presented) The anti-reflective coating forming composition according to claim 4, wherein the light absorbing compound is at least one compound selected from naphthalene compounds and anthracene compounds.

- 6. (Previously Presented) The anti-reflective coating forming composition according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.
- 7. (Previously Presented) The anti-reflective coating forming composition according to claim 4, wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.
- 8. (Previously Presented) The anti-reflective coating forming composition according to claim 1, further containing a resin having at lease one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.
 - 9. (Canceled)
- 10. (Previously Presented) A method of forming an anti-reflective coating for use in lithography process in a manufacture of a semiconductor device, characterized by comprising the steps of: coating anti-reflective coating forming composition according to claim 1 on a substrate, and baking it.
- 11. (Previously Presented) A process for manufacturing a semiconductor device, characterized by comprising the steps of:

coating anti-reflective coating forming composition according to claim 1 on a substrate and baking it to form an anti-reflective coating;

forming a photoresist on the anti-reflective coating;

exposing the substrate covered with the anti-reflective coating and the photoresist with a light;

developing it;

transferring an image on the substrate by etching to form an integrated circuit device.